

ABSTRACT OF THE DISCLOSURE

A process for producing a semiconductor wafer is based upon etching the semiconductor wafer with an etching medium flowing in a laminar flow along a direction of flow toward an edge of the semiconductor wafer. There is a protective shield arranged in front of the edge of the semiconductor wafer, so that the etching medium flows onto the protective shield and not onto the edge of the semiconductor wafer. There is also a process that has the semiconductor wafer being inclined with respect to the direction of flow of the etching medium, so that there is an angle of less than 180° between the direction of flow of the etching medium and a first side of the semiconductor wafer. Also, there is an angle of greater than 180° between the direction of flow of the etching medium and a second side of the semiconductor wafer, and the second side of the semiconductor wafer is subsequently polished.